

isc Silicon NPN Power Transistor

2SD1563

**DESCRIPTION**

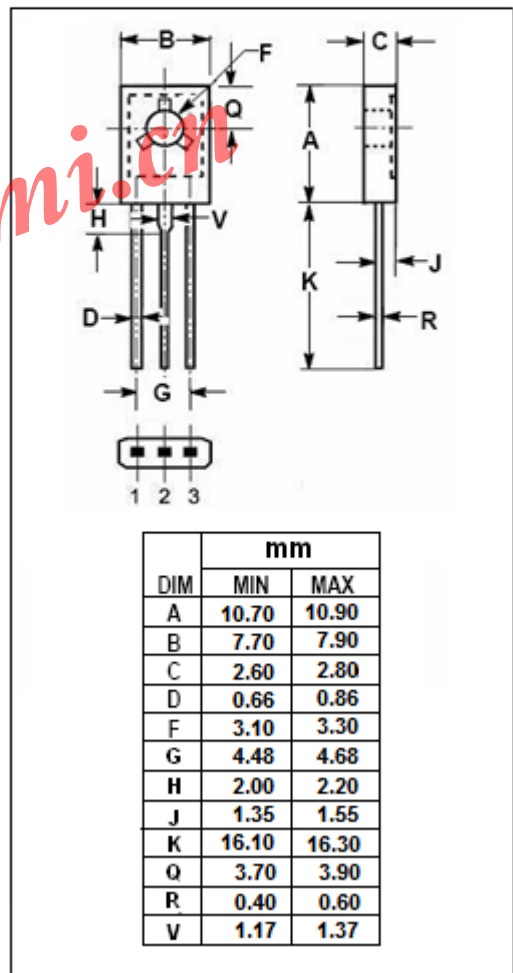
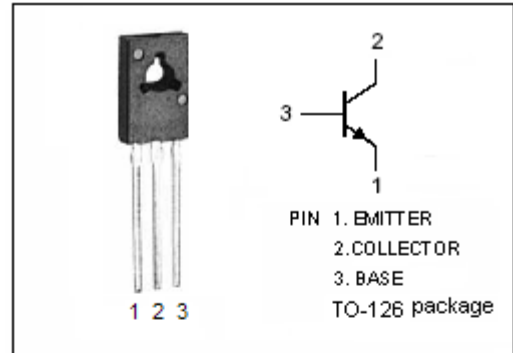
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 120V$  (Min)
- Wide Area of Safe Operation
- Complement to Type 2SB1086

**APPLICATIONS**

- Designed for low frequency power amplifier applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	120	V
$V_{CEO}$	Collector-Emitter Voltage	120	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
$I_C$	Collector Current-Continuous	1.5	A
$I_{CM}$	Collector Current-Peak	3	A
$P_C$	Total Power Dissipation @ $T_C=25^{\circ}C$	10	W
	Total Power Dissipation @ $T_a=25^{\circ}C$	1.2	
$T_J$	Junction Temperature	150	
$T_{stg}$	Storage Temperature Range	-55~150	$^{\circ}C$



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=1\text{mA}; I_B=0$	120			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=50\mu\text{A}; I_E=0$	120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=50\mu\text{A}; I_C=0$	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.1\text{A}$			2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.1\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=100\text{V}; I_E=0$			1.0	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=4\text{V}; I_C=0$			1.0	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C=0.1\text{A}; V_{CE}=5\text{V}$	56		390	
$f_T$	Current-Gain—Bandwidth Product	$I_C=0.1\text{A}; V_{CE}=5\text{V}$		80		MHz
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1\text{MHz}$		20		pF

◆  $h_{FE}$  Classifications

N	P	Q	R
56-120	82-180	120-270	180-390